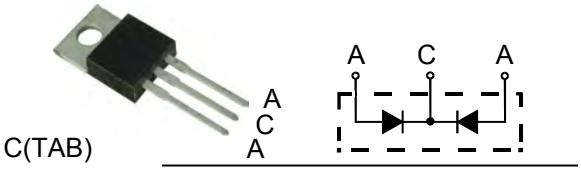
MUR1020CT

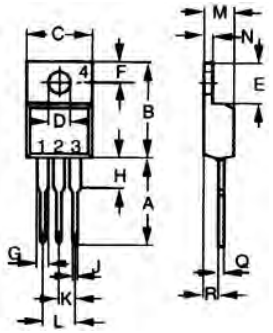
Ultra Fast Recovery Diodes



A=Anode, C=Cathode, TAB=Cathode

	V_{RRM} V	V_{RMS} V	V_{DC} V
MUR1020CT	200	140	200

Dimensions TO-220AB



Dim.	Inches		Milimeter	
	Min.	Max.	Min.	Max.
A	0.500	0.550	12.70	13.97
B	0.580	0.630	14.73	16.00
C	0.390	0.420	9.91	10.66
D	0.139	0.161	3.54	4.08
E	0.230	0.270	5.85	6.85
F	0.100	0.125	2.54	3.18
G	0.045	0.065	1.15	1.65
H	0.110	0.230	2.79	5.84
J	0.025	0.040	0.64	1.01
K	0.100	BSC	2.54	BSC
M	0.170	0.190	4.32	4.82
N	0.045	0.055	1.14	1.39
Q	0.014	0.022	0.35	0.56
R	0.090	0.110	2.29	2.79

Symbol	Characteristics		Maximum Ratings	Unit
$I_{(AV)}$	Maximum Average Forward Rectified Current	@T_C=125°C	10	A
I_{FSM}	Non Repetitive Peak Forward Surge Current Per Diode Sinusoidal (JEDEC METHOD)	T_P=10ms T_P=8.3ms	50 55	A
V_F	Maximum Forward Voltage Pulse Width=300us Duty Cycle	I_F=5A @T_J=25°C I_F=5A @T_J=125°C I_F=10A @T_J=25°C I_F=10A @T_J=125°C	0.975 0.925 1.25 1.20	V
I_R	Maximum DC Reverse Current At Rated DC Blocking Voltage	@T_J=25°C @T_J=100°C	5 100	uA
C_J	Typical Junction Capacitance Per Element (Note 1)		80	pF
T_{RR}	Maximum Reverse Recovery Time (Note 2)		30	ns
$R_{\theta JC}$	Typical Thermal Resistance		4.0	°C/W
T_J, T_{STG}	Operating And Storage Temperature Range		-55 to +150	°C

NOTES: 1. Measured at 1.0MHz And Applied Reverse Voltage Of 4.0V DC.
2. Reverse Recovery Test Conditions: I_F=0.5A, I_R=1.0A, I_{RR}=0.25A.

FEATURES

* Glass passivated chip
* Superfast switching time for high efficiency
* Low forward voltage drop and high current capability
* Low reverse leakage current
* High surge capacity
* RoHS compliant

MECHANICAL DATA

* Case: TO-220AB molded plastic
* Polarity: As marked on the body
* Weight: 0.08 ounces, 2.24 grams
* Mounting position: Any

Sirectifier®

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FIG.1 - FORWARD CURRENT DERATING CURVE

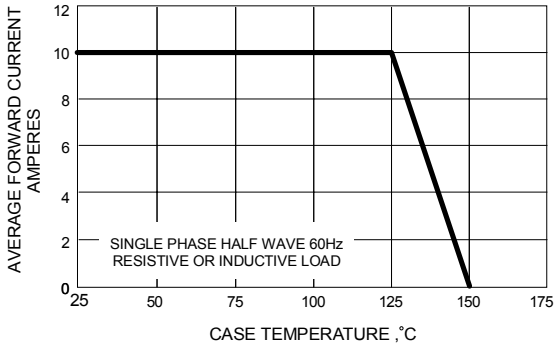


FIG.2 - MAXIMUM NON-REPETITIVE SURGE CURRENT

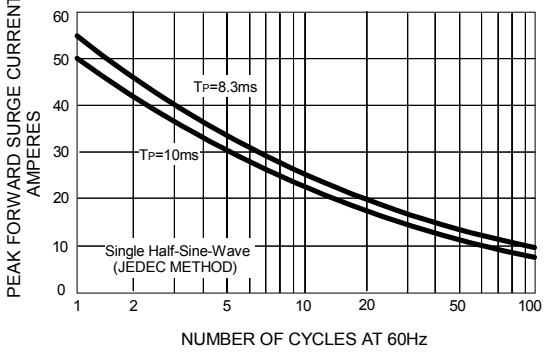


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

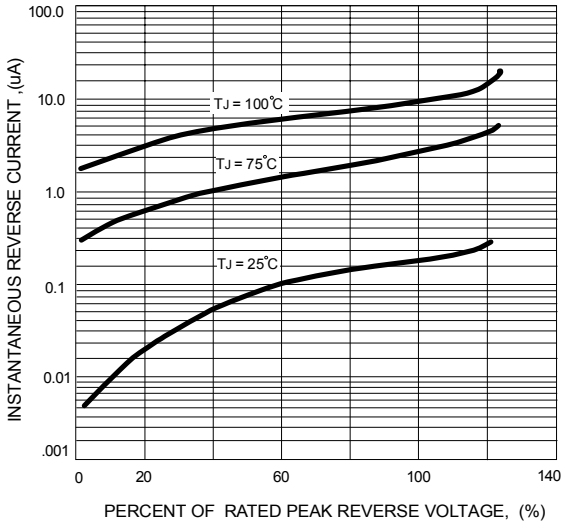


FIG.4 - TYPICAL FORWARD CHARACTERISTICS

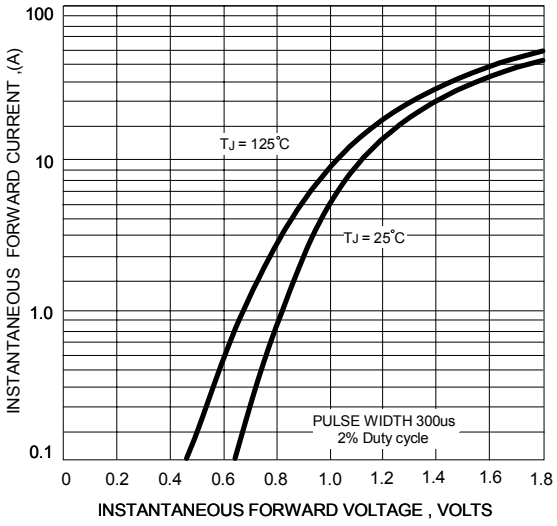
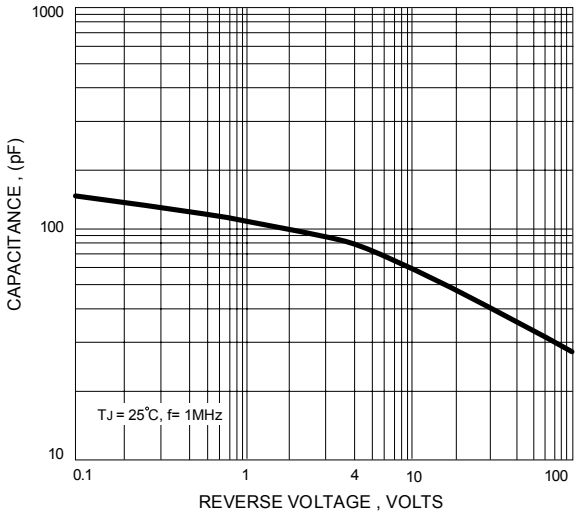


FIG.5 - TYPICAL JUNCTION CAPACITANCE



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